Dual N-Channel 25-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY				
	V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)[a, e]	Q_g (Typ)
Channel-1	25	0.023 at V_{GS} = 10 V	8.0	5.5
		0.028 at V_{GS} = 4.5 V	8.0	
Channel-2	25	0.023 at V_{GS} = 10 V	8.0	5.5
		0.028 at V_{GS} = 4.5 V	8.0	

SCHOTTKY PRODUCT SUMMARY		
V_{DS} (V)	V_{SD} (V) Diode Forward Voltage	I_F (A)[a]
25	0.43 V at 1.0 A	2.3

FEATURES

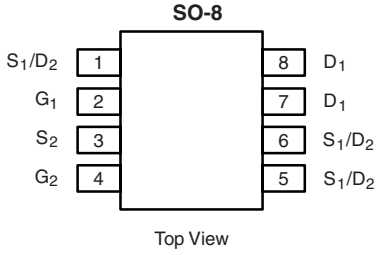
- TrenchFET® Power MOSFET
- PWM Optimized

APPLICATIONS

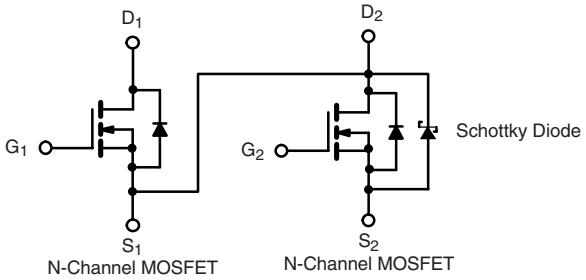
- Synchronous Buck Converter
- Game Machine
- Notebook

Pb-free

RoHS COMPLIANT



Ordering Information: Si4670DY-T1-E3 (Lead (Pb)-free)



ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**Channel-1**	**Channel-2**	**Unit**
Drain-Source Voltage		V_{DS}	25	25	V
Gate-Source Voltage		V_{GS}	± 16	± 16	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	8.0[e]	8.0[e]	A
	T_C = 70 °C		7	7	
	T_A = 25 °C		7[b, c]	7[b, c]	
	T_A = 70 °C		5.6[b, c]	5.6[b, c]	
Pulsed Drain Current (10 µs Pulse Width)		I_{DM}	30	30	
Source-Drain Current Diode Current	T_C = 25 °C	I_S	2.3	2.3	
	T_A = 25 °C		1.5[b, c]	1.5[b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	2.8	2.8	W
	T_C = 70 °C		1.8	1.8	
	T_A = 25 °C		1.8[b, c]	1.8[b, c]	
	T_A = 70 °C		1.1[b, c]	1.1[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS							
			Channel-1		**Channel-2**		
Parameter		**Symbol**	**Typ**	**Max**	**Typ**	**Max**	**Unit**
Maximum Junction-to-Ambient[b, d]	t ≤ 10 s	R_{thJA}	57	70	57	70	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	36	44	36	44	

Notes:
a. Based on T_C = 25 °C.
b. Surface Mounted on 1" x 1" FR4 Board.
c. t = 10 s.
d. Maximum under Steady State conditions is 110 °C/W (Channel-1 and Channel-2).
e. Package Limited.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted							
Parameter	**Symbol**	**Test Conditions**		**Min**	**Typ[a]**	**Max**	**Unit**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	Ch-1	25			V
		V_{GS} = 0 V, I_D = 250 µA	Ch-2	25			
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA	Ch-1		25		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I_D = 250 µA	Ch-1		- 4.7		
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	Ch-1	1		2.2	V
		V_{DS} = V_{GS}, I_D = 250 µA	Ch-2	1		2.2	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 16 V	Ch-1			100	nA
		V_{DS} = 0 V, V_{GS} = ± 16 V	Ch-2			100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 25 V, V_{GS} = 0 V	Ch-1			0.001	mA
		V_{DS} = 25 V, V_{GS} = 0 V	Ch-2		0.07	0.5	
		V_{DS} = 25 V, V_{GS} = 0 V, T_J = 100 °C	Ch-1			0.025	
		V_{DS} = 25 V, V_{GS} = 0 V, T_J = 100 °C	Ch-2		5	20	
On-State Drain Current[b]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	Ch-1	20			A
		$V_{DS} \geq$ 5 V, V_{GS} = 10 V	Ch-2	20			
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 7 A	Ch-1		0.019	0.023	Ω
		V_{GS} = 10 V, I_D = 7 A	Ch-2		0.019	0.023	
		V_{GS} = 4.5 V, I_D = 6.3 A	Ch-1		0.023	0.028	
		V_{GS} = 4.5 V, I_D = 6.3 A	Ch-2		0.023	0.028	
Forward Transconductance[b]	g_{fs}	V_{DS} = 10 V, I_D = 7 A	Ch-1		23		S
		V_{DS} = 10 V, I_D = 7 A	Ch-2		23		
Dynamic[a]							
Input Capacitance	C_{iss}	Channel-1 V_{DS} = 13 V, V_{GS} = 0 V, f = 1 MHz	Ch-1		680		pF
			Ch-2		680		
Output Capacitance	C_{oss}		Ch-1		120		
		Channel-2 V_{DS} = 13 V, V_{GS} = 0 V, f = 1 MHz	Ch-2		180		
Reverse Transfer Capacitance	C_{rss}		Ch-1		55		
			Ch-2		70		
Total Gate Charge	Q_g	V_{DS} = 13 V, V_{GS} = 10 V, I_D = 7 A	Ch-1		12	18	nC
		V_{DS} = 13 V, V_{GS} = 10 V, I_D = 7 A	Ch-2		12	18	
		Channel-1 V_{DS} = 13 V, V_{GS} = 4.5 V, I_D = 7 A	Ch-1		5.5	8.5	
			Ch-2		5.5	8.5	
Gate-Source Charge	Q_{gs}		Ch-1		2		
		Channel-2 V_{DS} = 13 V, V_{GS} = 4.5 V, I_D = 7 A	Ch-2		2		
Gate-Drain Charge	Q_{gd}		Ch-1		1.5		
			Ch-2		1.5		
Gate Resistance	R_g	f = 1 MHz	Ch-1		2.5		Ω
			Ch-2		2.5		

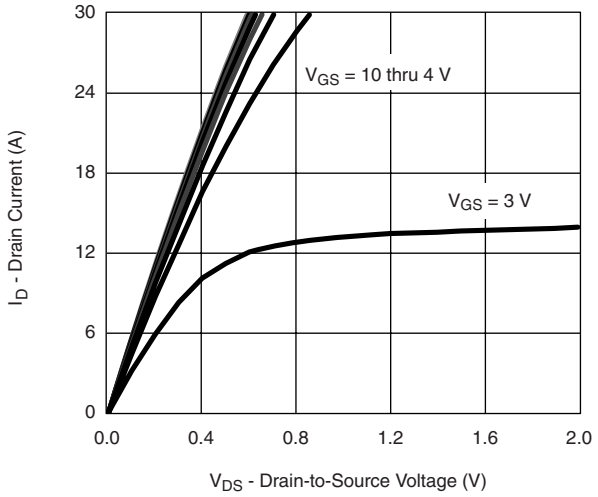
Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted							
Parameter	**Symbol**	**Test Conditions**		**Min**	**Typ[a]**	**Max**	**Unit**
Dynamic[a]							
Turn-On Delay Time	$t_{d(on)}$	Channel-1 V_{DD} = 13 V, R_L = 2.3 Ω $I_D \cong$ 5.6 A, V_{GEN} = 4.5 V, R_g = 1 Ω	Ch-1		15	25	ns
			Ch-2		15	25	
Rise Time	t_r		Ch-1		50	75	
			Ch-2		50	75	
Turn-Off Delay Time	$t_{d(off)}$	Channel-2 V_{DD} = 13 V, R_L = 2.3 Ω $I_D \cong$ 5.6 A, V_{GEN} = 4.5 V, R_g = 1 Ω	Ch-1		20	30	
			Ch-2		20	30	
Fall Time	t_f		Ch-1		10	15	
			Ch-2		10	15	
Turn-On Delay Time	$t_{d(on)}$	Channel-1 V_{DD} = 13 V, R_L = 2.3 Ω $I_D \cong$ 5.6 A, V_{GEN} = 10 V, R_g = 1 Ω	Ch-1		10	15	
			Ch-2		10	15	
Rise Time	t_r		Ch-1		12	20	
			Ch-2		12	20	
Turn-Off Delay Time	$t_{d(off)}$	Channel-2 V_{DD} = 13 V, R_L = 2.3 Ω $I_D \cong$ 5.6 A, V_{GEN} = 10 V, R_g = 1 Ω	Ch-1		15	25	
			Ch-2		15	25	
Fall Time	t_f		Ch-1		10	15	
			Ch-2		10	15	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C	Ch-1			2.3	A
			Ch-2			2.3	
Pulse Diode Forward Current[a]	I_{SM}		Ch-1			30	
			Ch-2			30	
Body Diode Voltage	V_{SD}	I_S = 5.6 A	Ch-1		0.8	1.2	V
		I_S = 1 A	Ch-2		0.37	0.43	
Body Diode Reverse Recovery Time	t_{rr}	Channel-1 I_F = 5.6 A, di/dt = 100 A/µs, T_J = 25 °C	Ch-1		15	30	ns
			Ch-2		15	30	
Body Diode Reverse Recovery Charge	Q_{rr}		Ch-1		8	16	nC
			Ch-2		8	16	
Reverse Recovery Fall Time	t_a	Channel-2 I_F = 5.6 A, di/dt = 100 A/µs, T_J = 25 °C	Ch-1		8.5		ns
			Ch-2		8.5		
Reverse Recovery Rise Time	t_b		Ch-1		6.5		
			Ch-2		6.5		

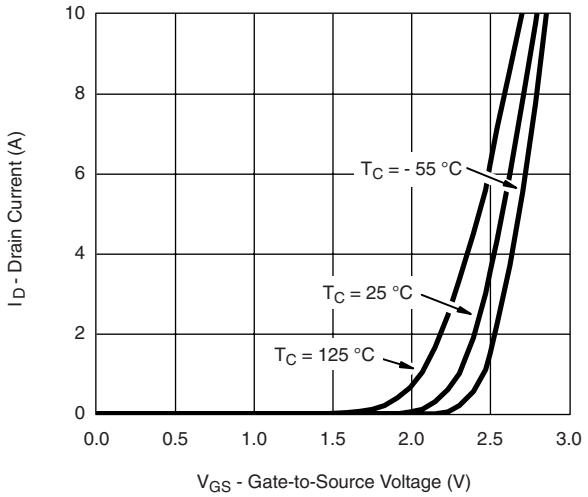
Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

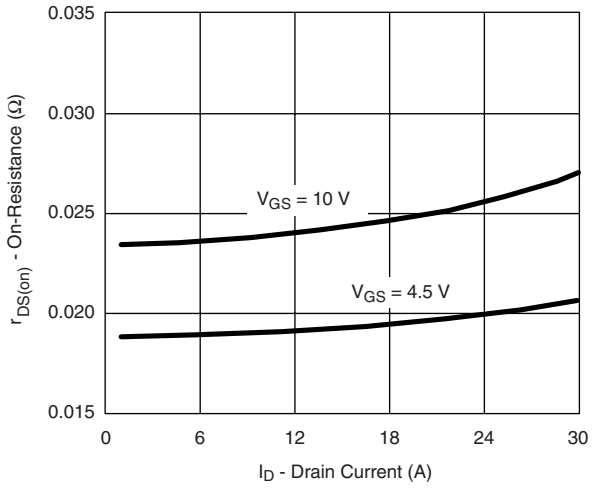
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



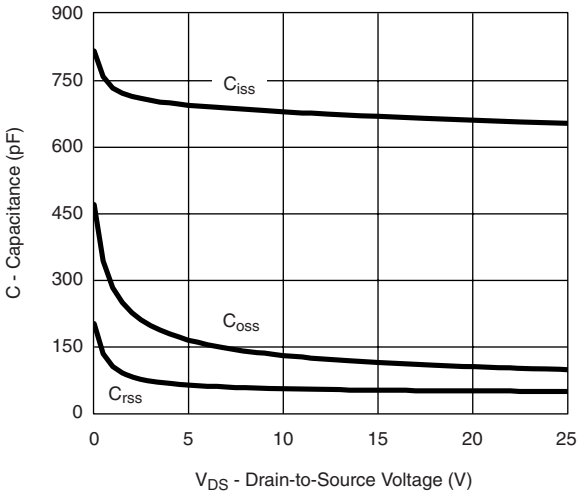
Output Characteristics



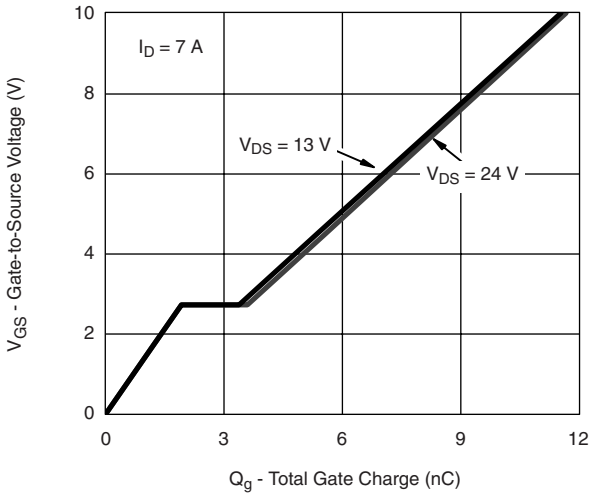
Transfer Characteristics



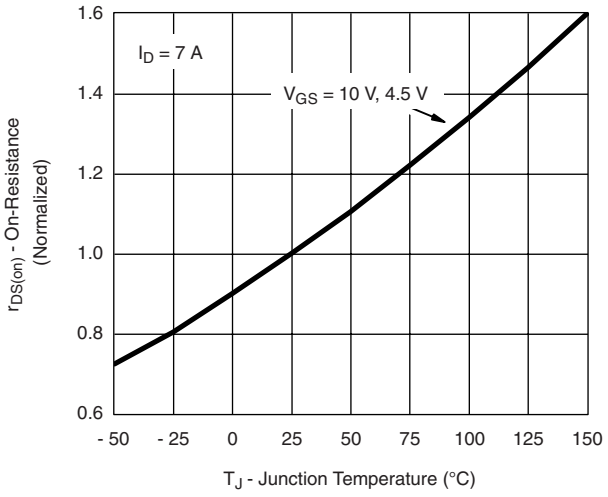
On-Resistance vs. Drain Current



Capacitance

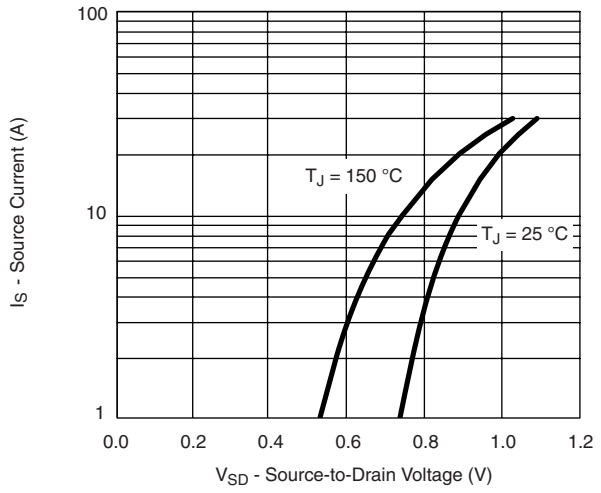


Gate Charge

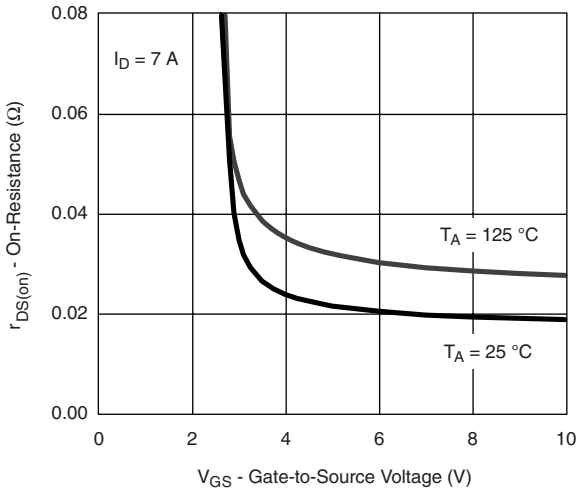


On-Resistance vs. Junction Temperature

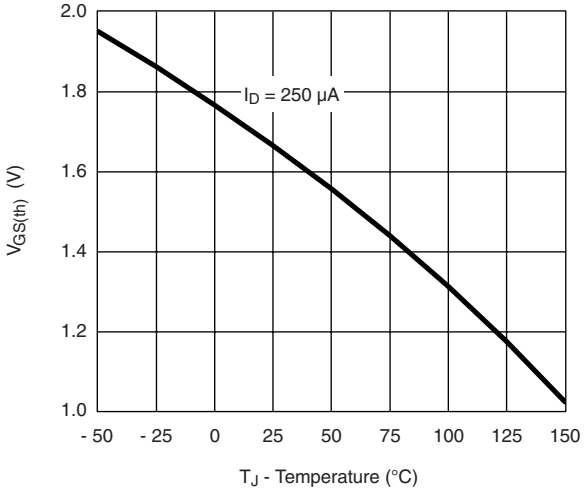
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



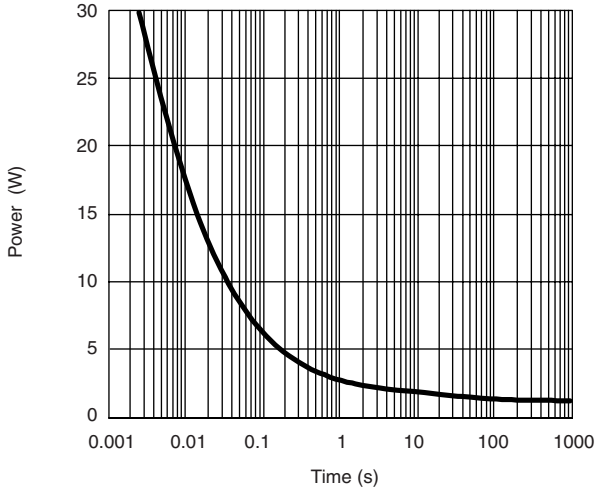
Source-Drain Diode Forward Voltage



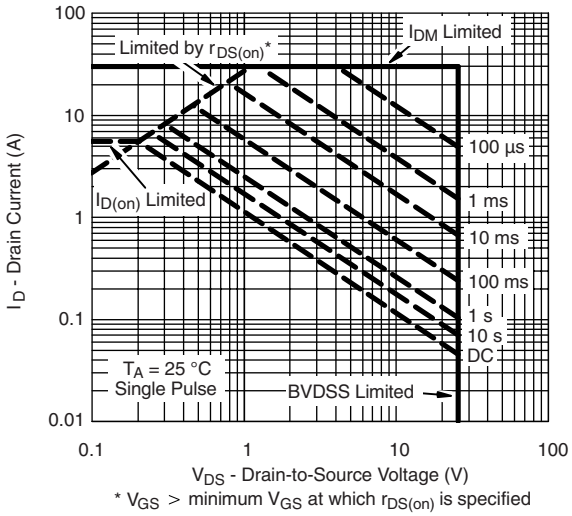
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

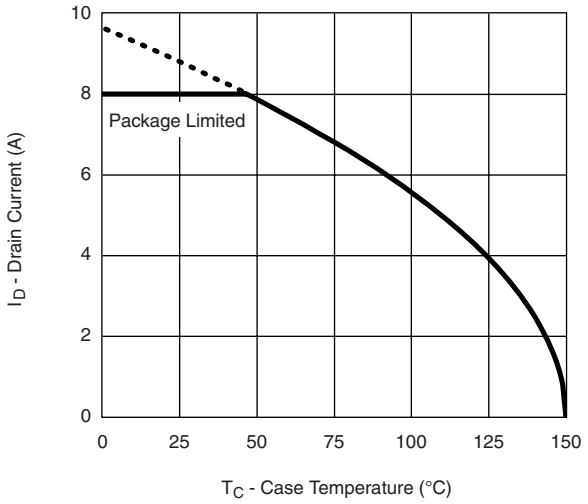


Single Pulse Power

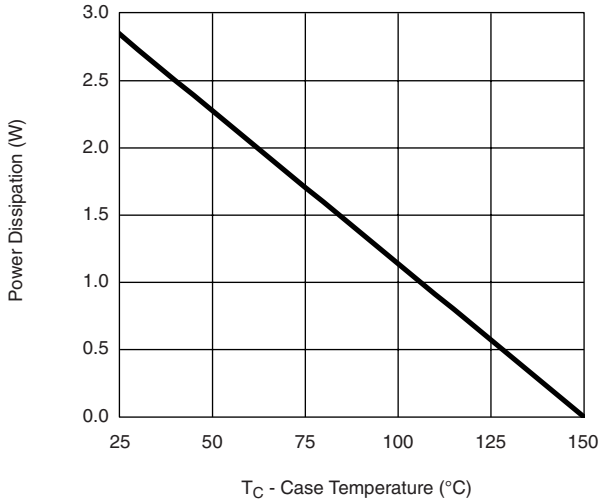


Safe Operating Area, Junction-to-Ambient

CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



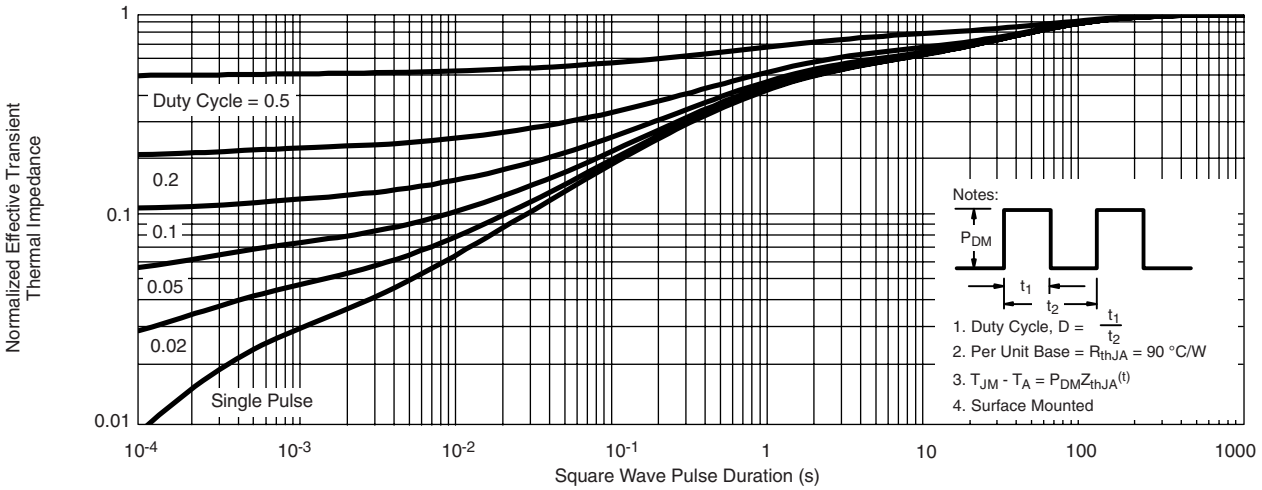
Current Derating*



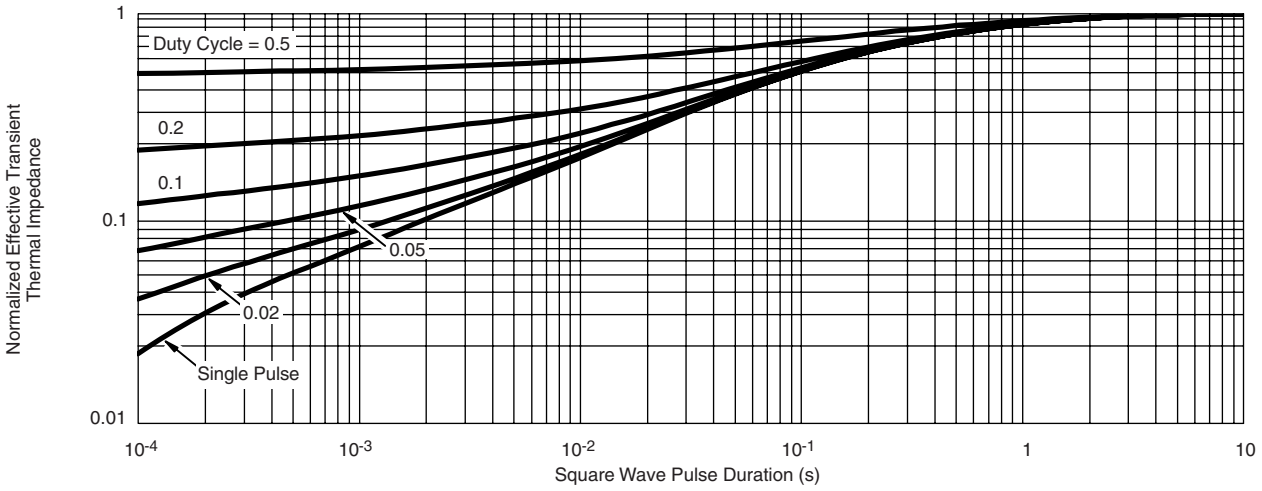
Power Derating

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

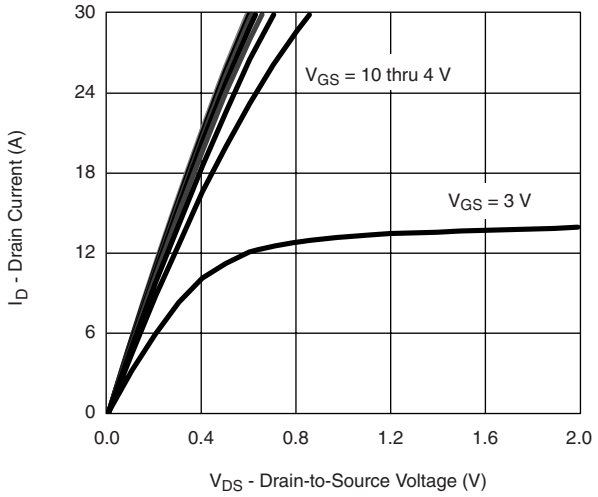


Normalized Thermal Transient Impedance, Junction-to-Ambient

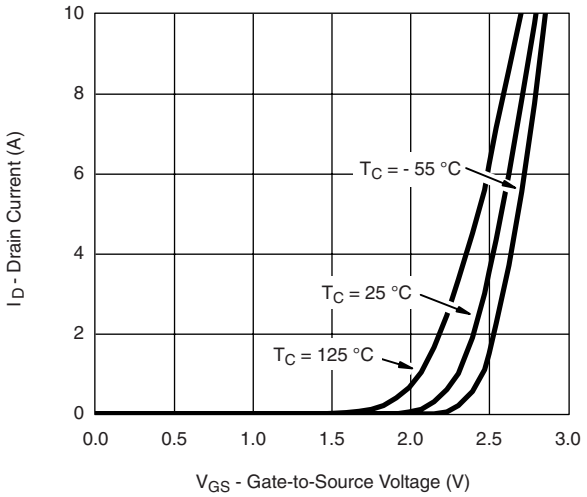


Normalized Thermal Transient Impedance, Junction-to-Foot

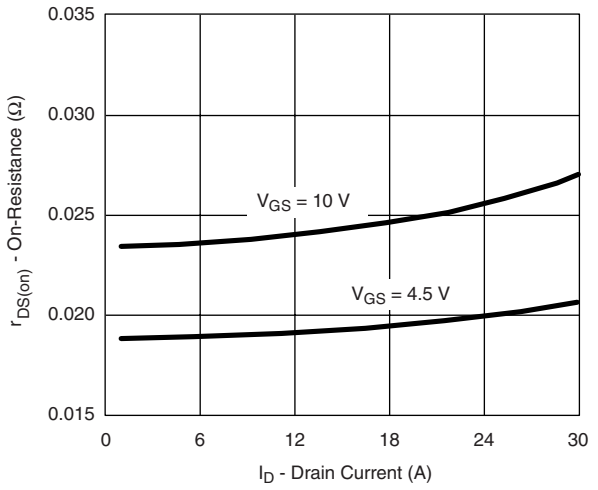
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



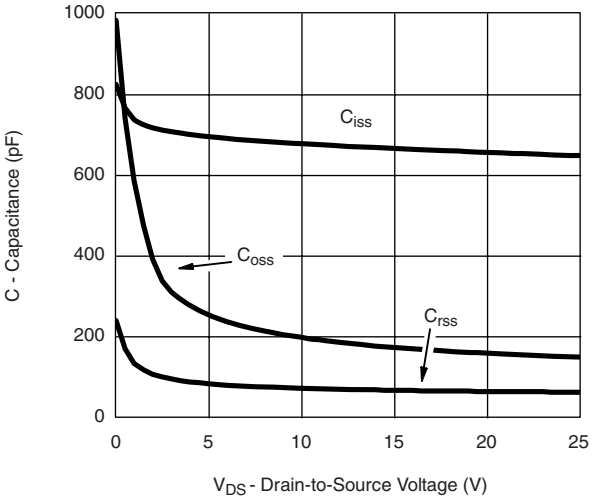
Output Characteristics



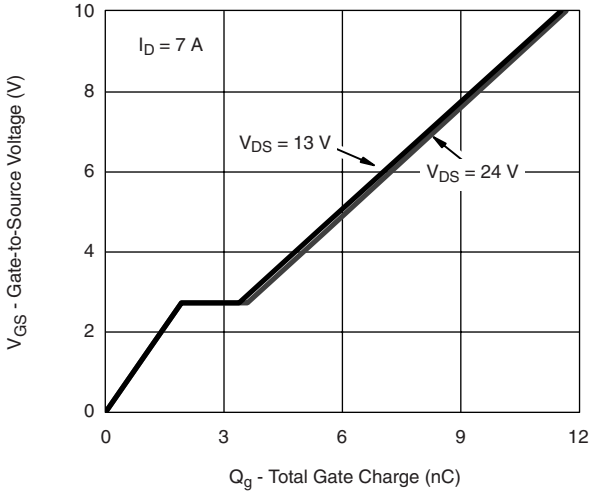
Transfer Characteristics



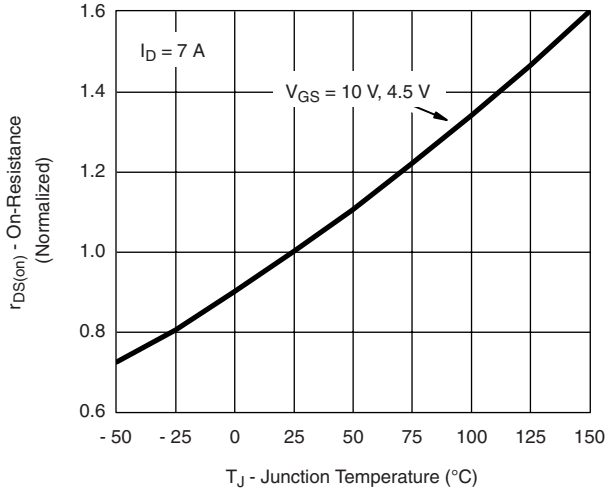
On-Resistance vs. Drain Current



Capacitance

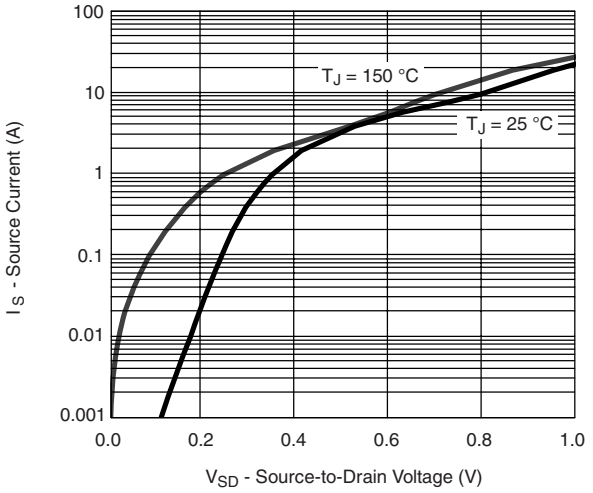


Gate Charge

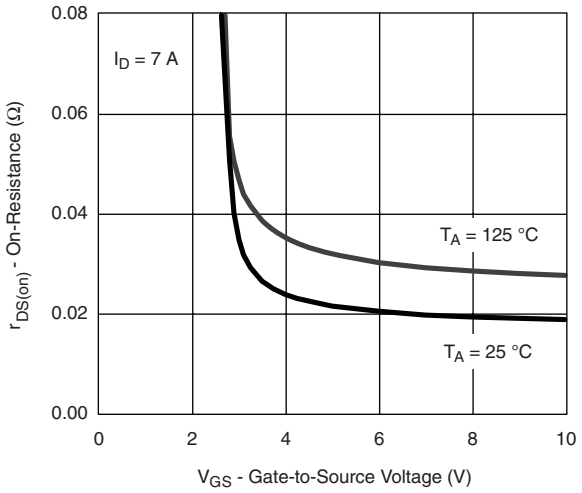


On-Resistance vs. Junction Temperature

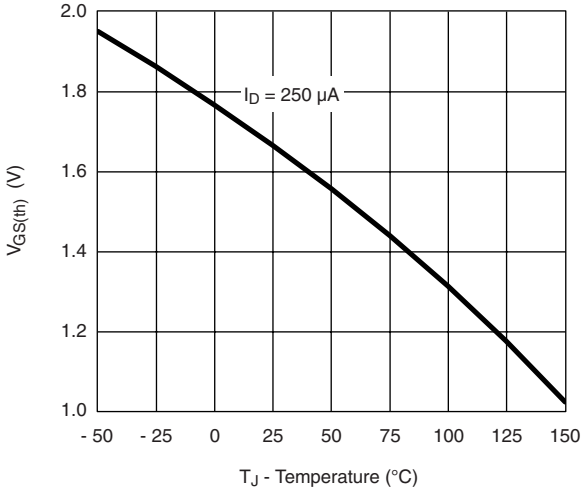
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



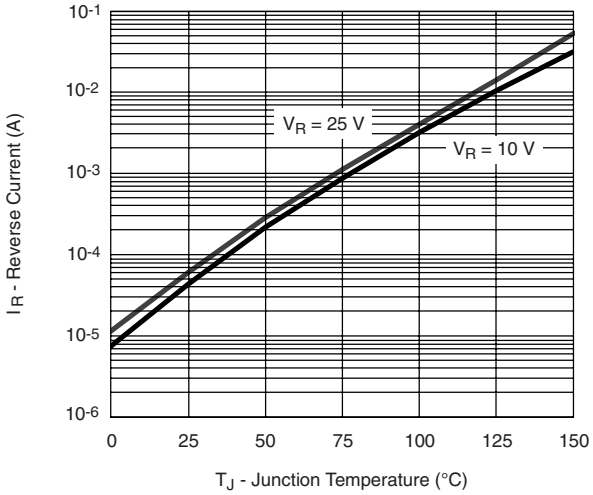
Source-Drain Diode Forward Voltage



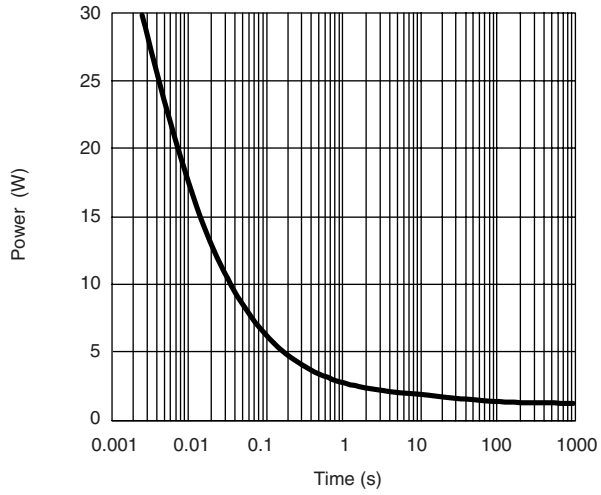
On-Resistance vs. Gate-to-Source Voltage



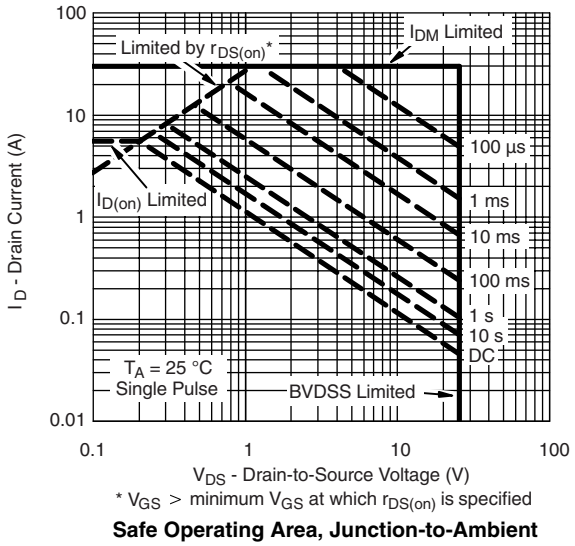
Threshold Voltage



Reverse Current vs. Junction Temperature

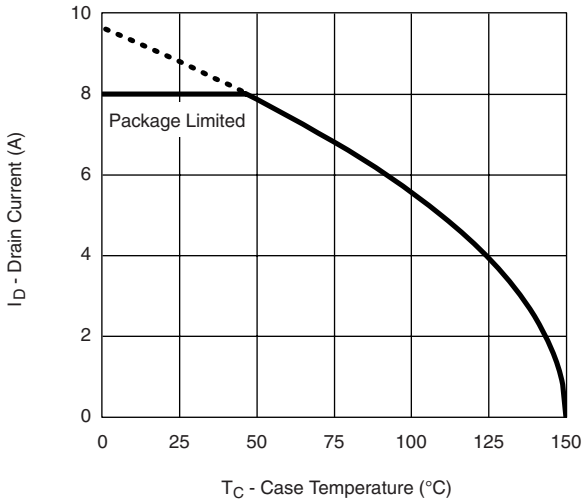


Single Pulse Power

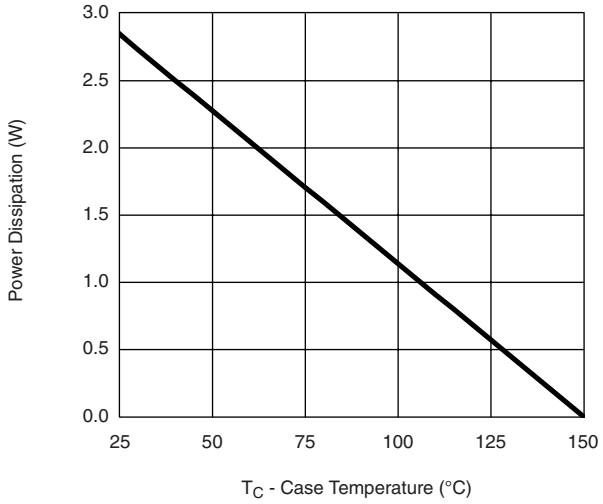


Safe Operating Area, Junction-to-Ambient

CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



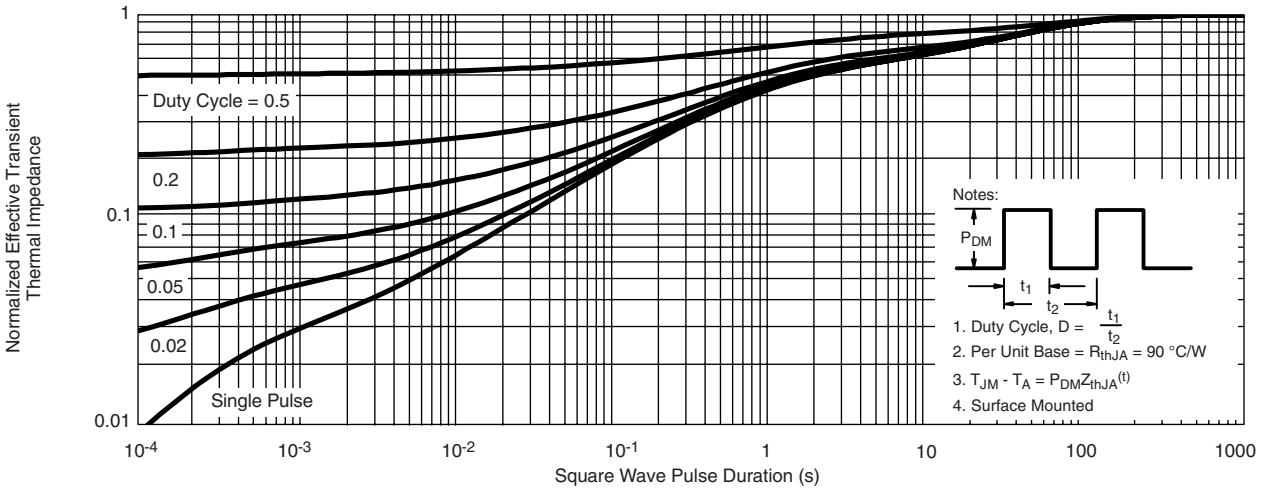
Current Derating*



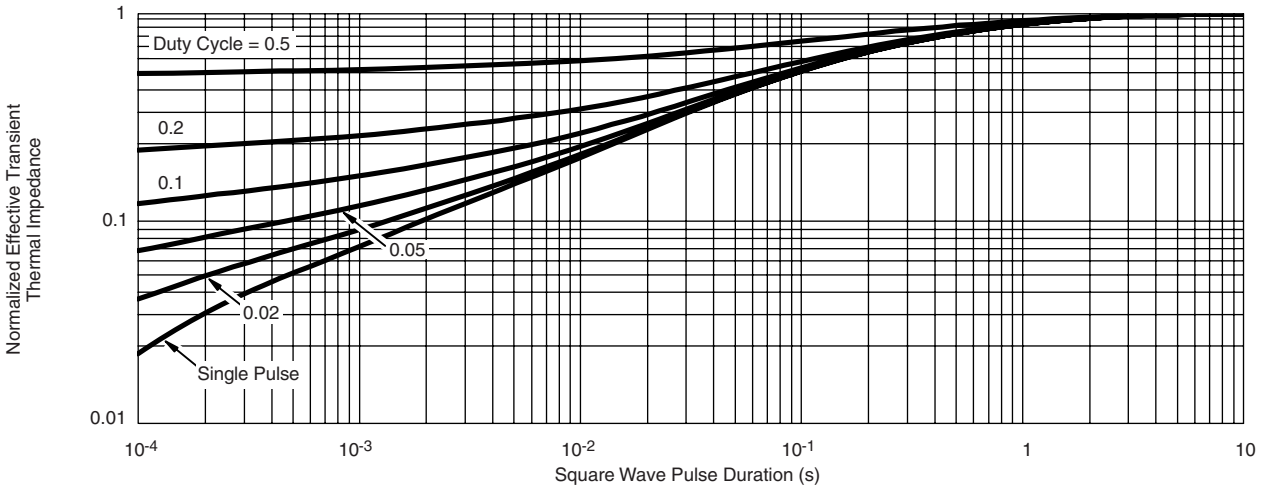
Power Derating

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?69595.

Notice

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.